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Sheet 2 of 2

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Application Number	To be assigned	10/525611
Filing Date	Herewith	
First Named Inventor	Henry W. White et al.	
Art Unit	To be assigned	
Examiner Name	To be assigned	
Attorney Docket Number	MOXT-002-US	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*		T ²
/A.R./	Ko, H.J. et al. "Photoluminescence properties of ZnO epilayers grown on CaF ₂ (111) by plasma assisted molecular beam epitaxy." Applied Physics Letters, Volume 76, Number 14, April 3, 2000, pp. 1905-1907.	
	Ryu, Y.R. et al. "Properties of arsenic-doped p-type ZnO grown by hybrid beam deposition." Applied Physics Letters, Volume 83, Number 1, July 7, 2003, pp. 87-89.	
	Ryu, Y.R. et al. "Synthesis of p-type ZnO films." Journal of Crystal Growth, 216 (2000), pp. 330-334.	
	Kumano, H. et al. "Luminescence properties of ZnO films grown on GaAs substrates by molecular-beam epitaxy excited by electron-cyclotron resonance oxygen plasma." Journal of Crystal Growth 214/215 (2000), pp. 280-283.	
	López, J. García et al. "Role of the oxygen plasma during in situ growth of YBa ₂ Cu ₃ O _{6+x} thin films by pulsed laser deposition." Physica C 307 (1998), pp. 298-306.	
	Tsurumi, Takaaki et al. "Electric Properties of Zinc Oxide Epitaxial Films Grown by Ion-Beam Sputtering with Oxygen-Radical Irradiation." Japanese Journal of Applied Physics, Vol. 38 (1999), pp. 3682-3688.	
	Ryu, Y.R. et al. "Fabrication of homostructural ZnO p-n junctions." Journal of Crystal Growth 219 (2000), pp.419-422.	

Examiner Signature	/Angel Roman/	Date Considered	06/27/2010
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